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Kind regards,

Team Nexperia

# PEMH2; PUMH2

NPN/NPN resistor-equipped transistors;  
R1 = 47 k $\Omega$ , R2 = 47 k $\Omega$

Rev. 5 — 5 December 2011

Product data sheet

## 1. Product profile

### 1.1 General description

NPN/NPN double Resistor-Equipped Transistors (RET) in Surface-Mounted Device (SMD) plastic packages.

Table 1. Product overview

Type number	Package		NPN/PNP complement	PNP/PNP complement	Package configuration
	NXP	JEITA			
PEMH2	SOT666	-	PEMD12	PEMB2	ultra small and flat lead
PUMH2	SOT363	SC-88	PUMD12	PUMB2	very small

### 1.2 Features and benefits

- 100 mA output current capability
- Built-in bias resistors
- Simplifies circuit design
- Reduces component count
- Reduces pick and place costs
- AEC-Q101 qualified

### 1.3 Applications

- Low current peripheral driver
- Control of IC inputs
- Replaces general-purpose transistors in digital applications

### 1.4 Quick reference data

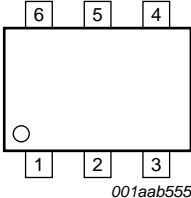
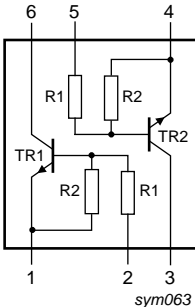
Table 2. Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>Per transistor</b>						
V <sub>CEO</sub>	collector-emitter voltage	open base	-	-	50	V
I <sub>O</sub>	output current		-	-	100	mA
R1	bias resistor 1 (input)		33	47	61	k $\Omega$
R2/R1	bias resistor ratio		0.8	1	1.2	



## 2. Pinning information

Table 3. Pinning

Pin	Description	Simplified outline	Graphic symbol
1	GND (emitter) TR1		
2	input (base) TR1		
3	output (collector) TR2		
4	GND (emitter) TR2		
5	input (base) TR2		
6	output (collector) TR1		

## 3. Ordering information

Table 4. Ordering information

Type number	Package		Version
	Name	Description	
PEMH2	-	plastic surface-mounted package; 6 leads	SOT666
PUMH2	SC-88	plastic surface-mounted package; 6 leads	SOT363

## 4. Marking

Table 5. Marking codes

Type number	Marking code <sup>[1]</sup>
PEMH2	Z2
PUMH2	2*H

[1] \* = placeholder for manufacturing site code

## 5. Limiting values

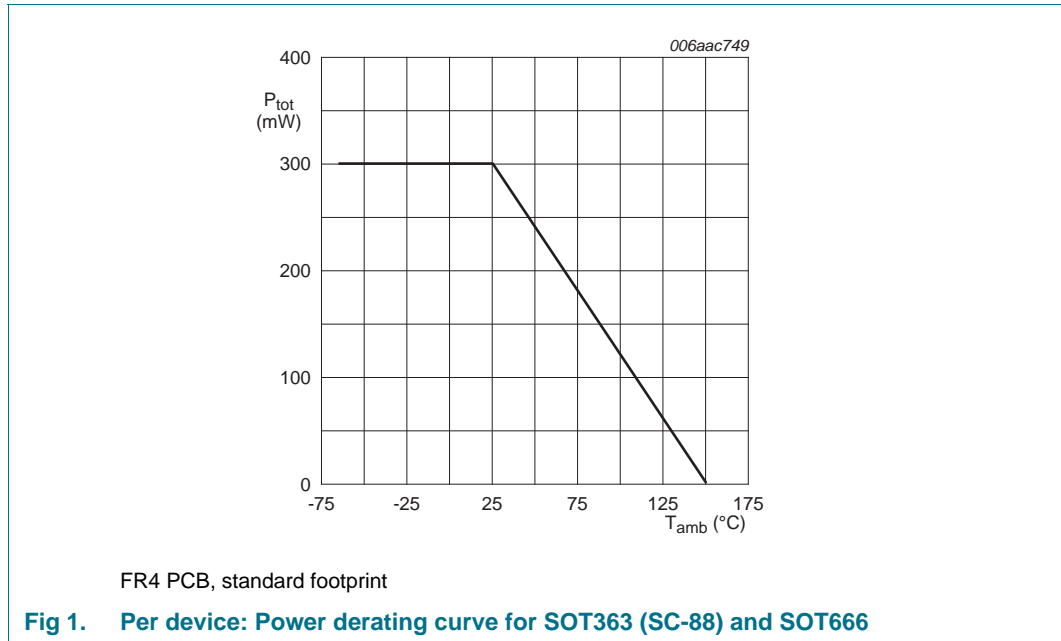
**Table 6. Limiting values**

*In accordance with the Absolute Maximum Rating System (IEC 60134).*

Symbol	Parameter	Conditions	Min	Max	Unit	
<b>Per transistor</b>						
V <sub>CBO</sub>	collector-base voltage	open emitter	-	50	V	
V <sub>CEO</sub>	collector-emitter voltage	open base	-	50	V	
V <sub>EBO</sub>	emitter-base voltage	open collector	-	10	V	
V <sub>I</sub>	input voltage					
	positive		-	+40	V	
	negative		-	-10	V	
I <sub>O</sub>	output current		-	100	mA	
I <sub>CM</sub>	peak collector current	single pulse; t <sub>p</sub> ≤ 1 ms	-	100	mA	
P <sub>tot</sub>	total power dissipation		T <sub>amb</sub> ≤ 25 °C			
	PEMH2 (SOT666)		[1][2]	-	200	mW
	PUMH2 (SOT363)		[1]	-	200	mW
<b>Per device</b>						
P <sub>tot</sub>	total power dissipation		T <sub>amb</sub> ≤ 25 °C			
	PEMH2 (SOT666)		[1][2]	-	300	mW
	PUMH2 (SOT363)		[1]	-	300	mW
T <sub>j</sub>	junction temperature		-	150	°C	
T <sub>amb</sub>	ambient temperature		-65	+150	°C	
T <sub>stg</sub>	storage temperature		-65	+150	°C	

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

[2] Reflow soldering is the only recommended soldering method.



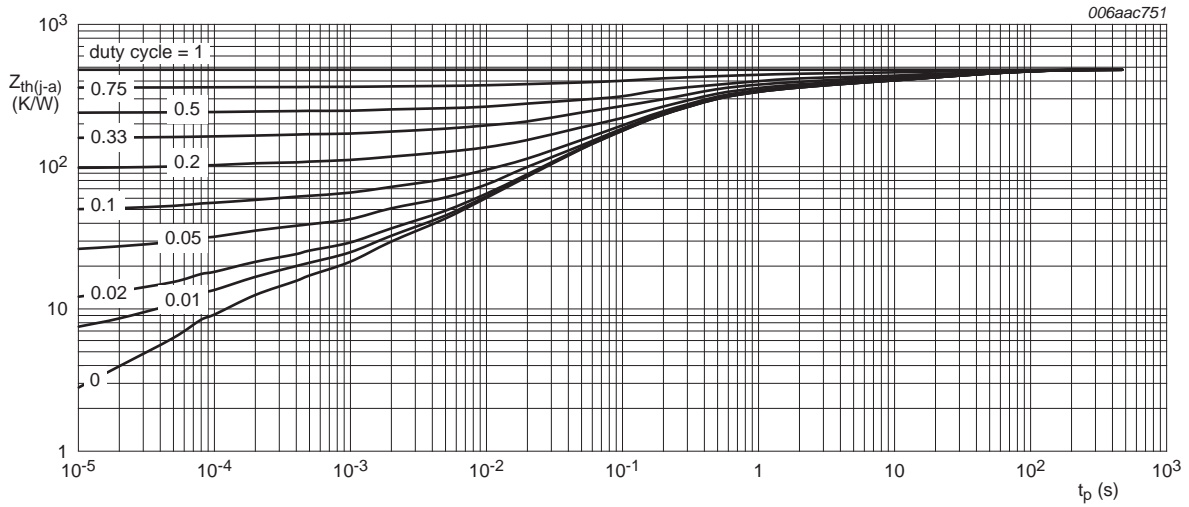
## 6. Thermal characteristics

**Table 7. Thermal characteristics**

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>Per transistor</b>						
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air				
	PEMH2 (SOT666)		[1][2]	-	625	K/W
	PUMH2 (SOT363)		[1]	-	625	K/W
<b>Per device</b>						
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air				
	PEMH2 (SOT666)		[1][2]	-	417	K/W
	PUMH2 (SOT363)		[1]	-	417	K/W

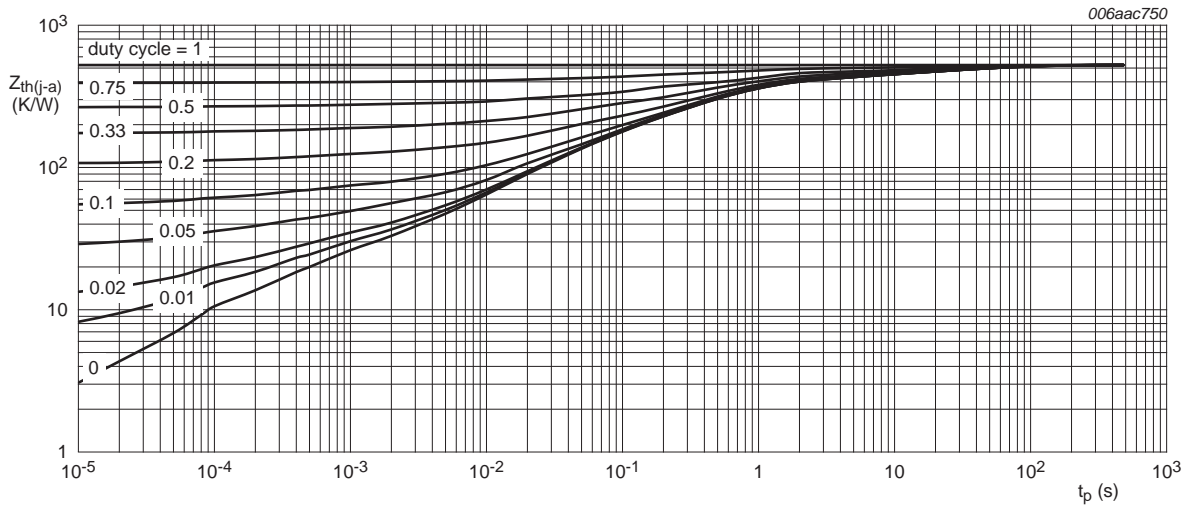
[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[2] Reflow soldering is the only recommended soldering method.



FR4 PCB, standard footprint

**Fig 2. Per transistor: Transient thermal impedance from junction to ambient as a function of pulse duration for PEMH2 (SOT666); typical values**



FR4 PCB, standard footprint

**Fig 3. Per transistor: Transient thermal impedance from junction to ambient as a function of pulse duration for PUMH2 (SOT363); typical values**

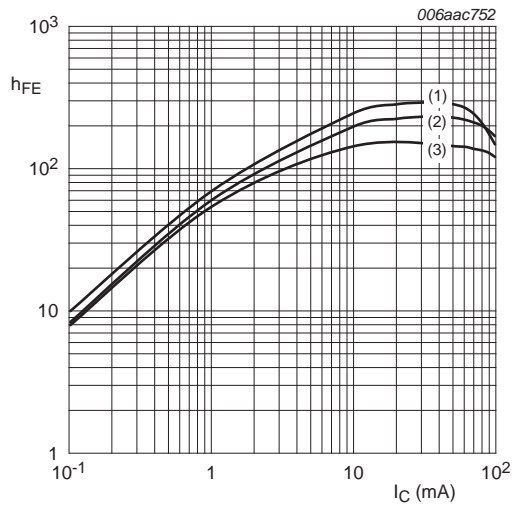
## 7. Characteristics

**Table 8. Characteristics**

$T_{amb} = 25\text{ }^{\circ}\text{C}$  unless otherwise specified.

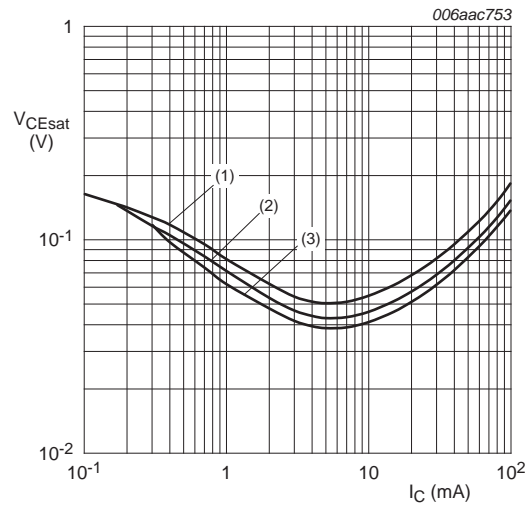
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>Per transistor</b>						
$I_{CBO}$	collector-base cut-off current	$V_{CB} = 50\text{ V}; I_E = 0\text{ A}$	-	-	100	nA
$I_{CEO}$	collector-emitter cut-off current	$V_{CE} = 30\text{ V}; I_B = 0\text{ A}$	-	-	1	$\mu\text{A}$
		$V_{CE} = 30\text{ V}; I_B = 0\text{ A}; T_j = 150\text{ }^{\circ}\text{C}$	-	-	5	$\mu\text{A}$
$I_{EBO}$	emitter-base cut-off current	$V_{EB} = 5\text{ V}; I_C = 0\text{ A}$	-	-	90	$\mu\text{A}$
$h_{FE}$	DC current gain	$V_{CE} = 5\text{ V}; I_C = 5\text{ mA}$	80	-	-	
$V_{CEsat}$	collector-emitter saturation voltage	$I_C = 10\text{ mA}; I_B = 0.5\text{ mA}$	-	-	150	mV
$V_{I(off)}$	off-state input voltage	$V_{CE} = 5\text{ V}; I_C = 100\text{ }\mu\text{A}$	-	1.2	0.8	V
$V_{I(on)}$	on-state input voltage	$V_{CE} = 0.3\text{ V}; I_C = 2\text{ mA}$	3	1.6	-	V
R1	bias resistor 1 (input)		33	47	61	k $\Omega$
R2/R1	bias resistor ratio		0.8	1	1.2	
$C_c$	collector capacitance	$V_{CB} = 10\text{ V}; I_E = i_e = 0\text{ A}; f = 1\text{ MHz}$			2.5	pF
$f_T$	transition frequency	$V_{CE} = 5\text{ V}; I_C = 10\text{ mA}; f = 100\text{ MHz}$	[1]	230		MHz

[1] Characteristics of built-in transistor



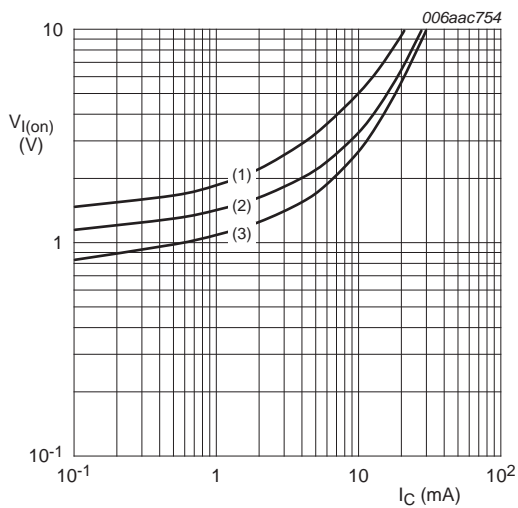
$V_{CE} = 5\text{ V}$   
 (1)  $T_{amb} = 100\text{ }^{\circ}\text{C}$   
 (2)  $T_{amb} = 25\text{ }^{\circ}\text{C}$   
 (3)  $T_{amb} = -40\text{ }^{\circ}\text{C}$

**Fig 4. DC current gain as a function of collector current; typical values**



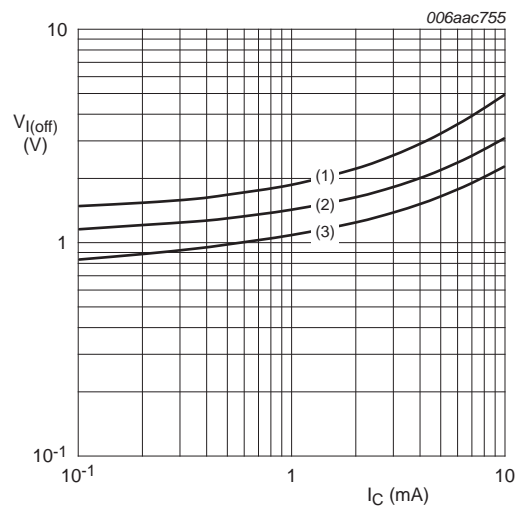
$I_C/I_B = 20$   
 (1)  $T_{amb} = 100\text{ }^{\circ}\text{C}$   
 (2)  $T_{amb} = 25\text{ }^{\circ}\text{C}$   
 (3)  $T_{amb} = -40\text{ }^{\circ}\text{C}$

**Fig 5. Collector-emitter saturation voltage as a function of collector current; typical values**



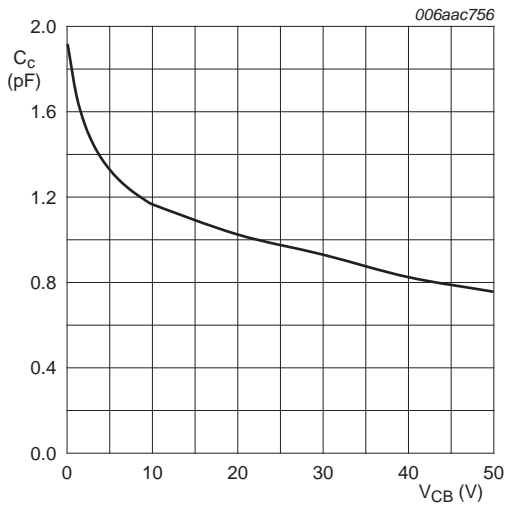
$V_{CE} = 0.3\text{ V}$   
 (1)  $T_{amb} = -40\text{ }^{\circ}\text{C}$   
 (2)  $T_{amb} = 25\text{ }^{\circ}\text{C}$   
 (3)  $T_{amb} = 100\text{ }^{\circ}\text{C}$

**Fig 6. On-state input voltage as a function of collector current; typical values**



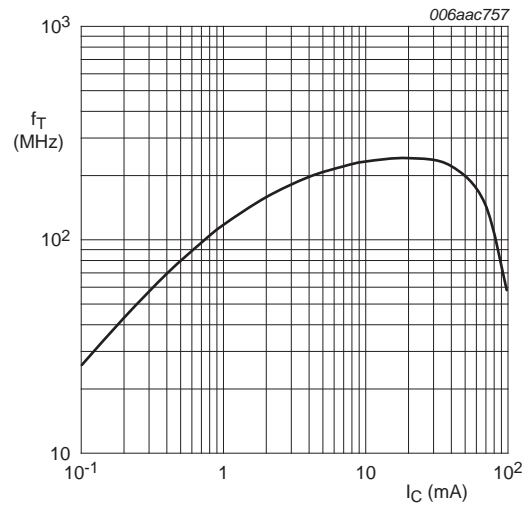
$V_{CE} = 5\text{ V}$   
 (1)  $T_{amb} = -40\text{ }^{\circ}\text{C}$   
 (2)  $T_{amb} = 25\text{ }^{\circ}\text{C}$   
 (3)  $T_{amb} = 100\text{ }^{\circ}\text{C}$

**Fig 7. Off-state input voltage as a function of collector current; typical values**



f = 1 MHz; T<sub>amb</sub> = 25 °C

**Fig. 8. Collector capacitance as a function of collector-base voltage; typical values**



V<sub>CE</sub> = 5 V; T<sub>amb</sub> = 25 °C

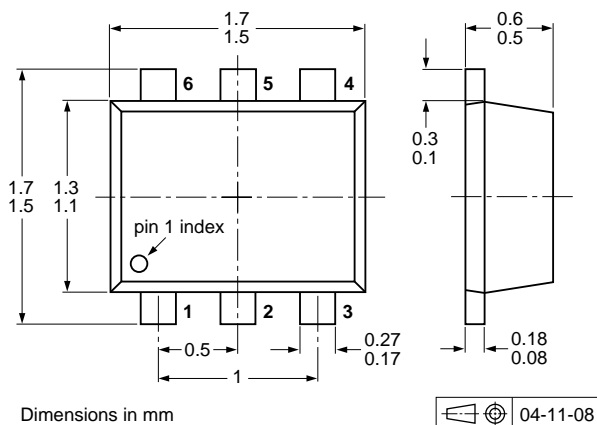
**Fig. 9. Transition frequency as a function of collector current; typical values of built-in transistor**

## 8. Test information

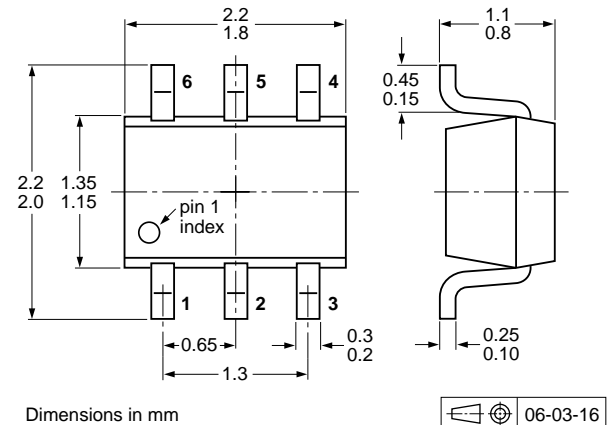
### 8.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - *Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

## 9. Package outline



**Fig. 10. Package outline PEMH2 (SOT666)**



**Fig. 11. Package outline PUMH2 (SOT363)**

10. Packing information

Table 9. Packing methods

The indicated -xxx are the last three digits of the 12NC ordering code.<sup>[1]</sup>

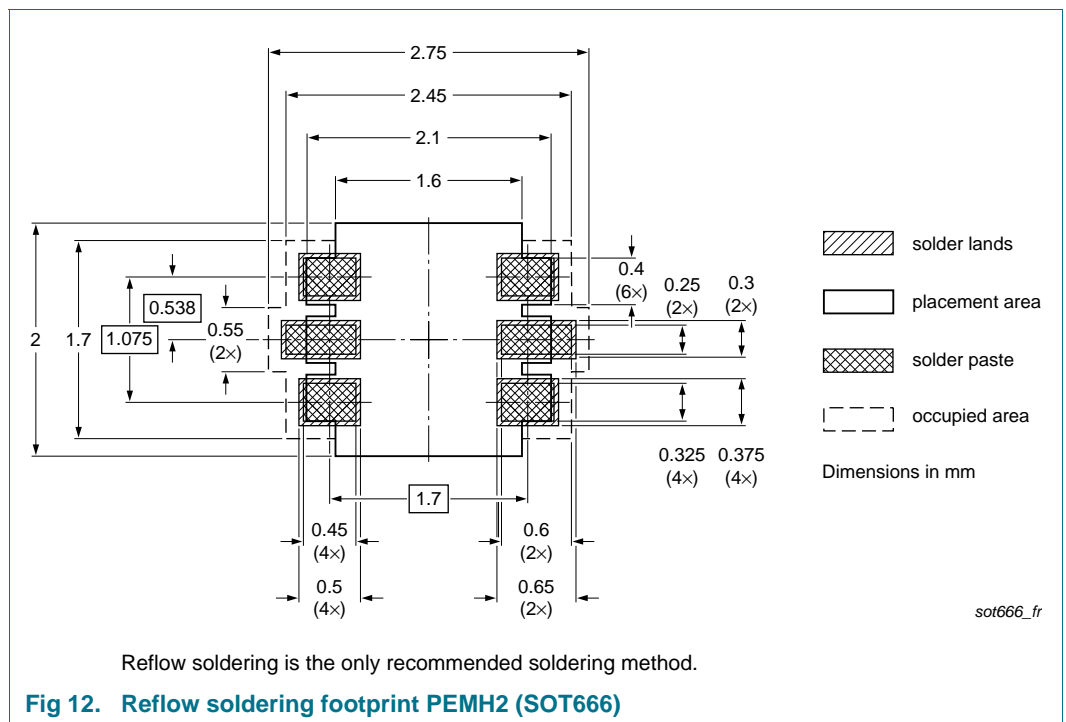
Type number	Package	Description	Packing quantity			
			3000	4000	8000	10000
PEMH2	SOT666	2 mm pitch, 8 mm tape and reel	-	-	-315	-
		4 mm pitch, 8 mm tape and reel	-	-115	-	-
PUMH2	SOT363	4 mm pitch, 8 mm tape and reel; T1 <sup>[2]</sup>	-115	-	-	-135
		4 mm pitch, 8 mm tape and reel; T2 <sup>[3]</sup>	-125	-	-	-165

[1] For further information and the availability of packing methods, see [Section 14](#).

[2] T1: normal taping

[3] T2: reverse taping

11. Soldering



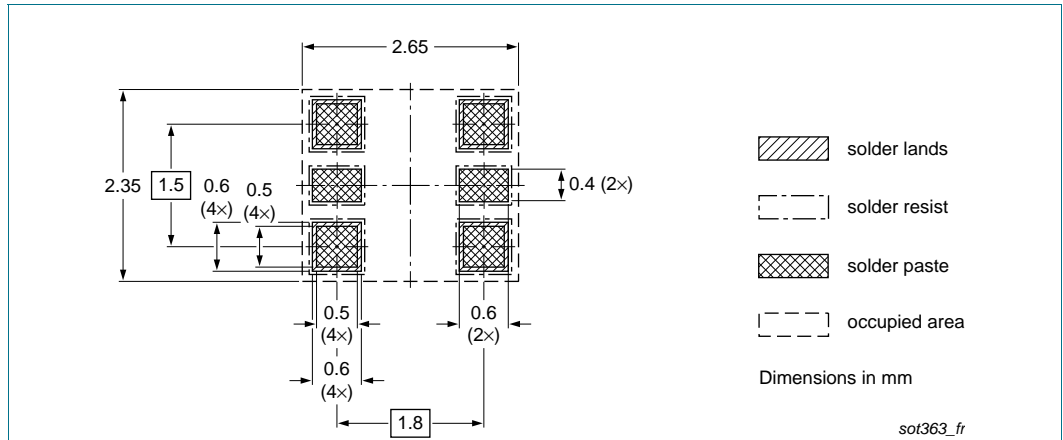


Fig 13. Reflow soldering footprint PUMH2 (SOT363)

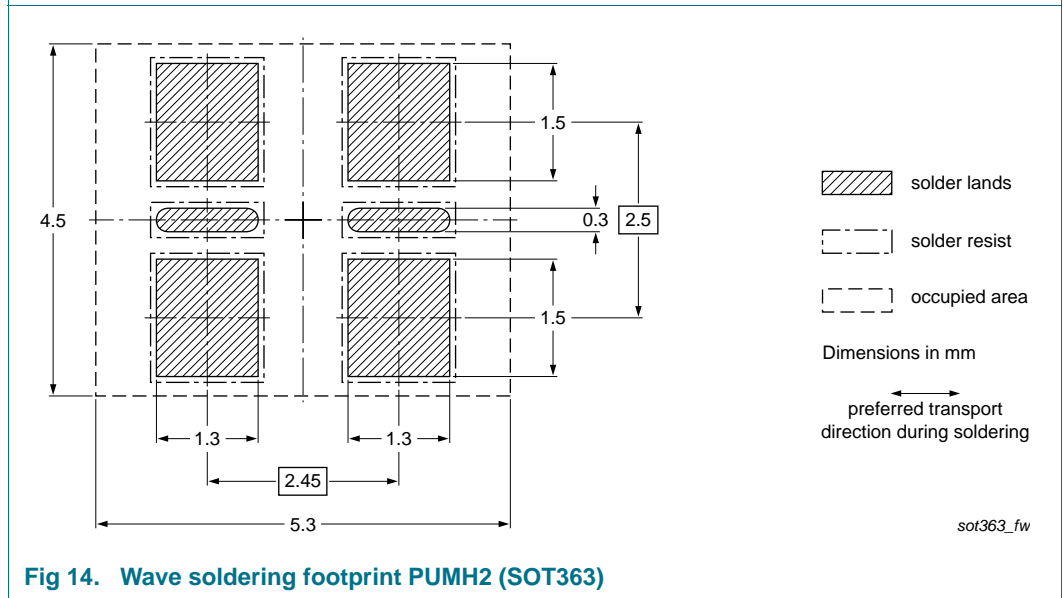


Fig 14. Wave soldering footprint PUMH2 (SOT363)

## 12. Revision history

**Table 10. Revision history**

Document ID	Release date	Data sheet status	Change notice	Supersedes
PEMH2_PUMH2 v.5	20111205	Product data sheet	-	PEMH2_PUMH2 v.4
Modifications:	• <a href="#">Table 1 “Product overview”</a> : corrected			
PEMH2_PUMH2 v.4	20111116	Product data sheet	-	PEMH2_PUMH2 v.3
PEMH2_PUMH2 v.3	20040414	Product data sheet	-	PEMH2_PUMH2 v.2
PEMH2_PUMH2 v.2	20031002	Product specification	-	PEMH2 v.1 PUMH2 v.1
PEMH2 v.1	20011022	Preliminary specification	-	-
PUMH2 v.1	19990803	Product specification	-	-

## 13. Legal information

### 13.1 Data sheet status

Document status <sup>[1][2]</sup>	Product status <sup>[3]</sup>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions".
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## 15. Contents

<b>1</b>	<b>Product profile</b> .....	<b>1</b>
1.1	General description .....	1
1.2	Features and benefits .....	1
1.3	Applications .....	1
1.4	Quick reference data .....	1
<b>2</b>	<b>Pinning information</b> .....	<b>2</b>
<b>3</b>	<b>Ordering information</b> .....	<b>2</b>
<b>4</b>	<b>Marking</b> .....	<b>2</b>
<b>5</b>	<b>Limiting values</b> .....	<b>3</b>
<b>6</b>	<b>Thermal characteristics</b> .....	<b>4</b>
<b>7</b>	<b>Characteristics</b> .....	<b>6</b>
<b>8</b>	<b>Test information</b> .....	<b>8</b>
8.1	Quality information .....	8
<b>9</b>	<b>Package outline</b> .....	<b>8</b>
<b>10</b>	<b>Packing information</b> .....	<b>9</b>
<b>11</b>	<b>Soldering</b> .....	<b>9</b>
<b>12</b>	<b>Revision history</b> .....	<b>11</b>
<b>13</b>	<b>Legal information</b> .....	<b>12</b>
13.1	Data sheet status .....	12
13.2	Definitions .....	12
13.3	Disclaimers .....	12
13.4	Trademarks .....	13
<b>14</b>	<b>Contact information</b> .....	<b>13</b>
<b>15</b>	<b>Contents</b> .....	<b>14</b>

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